

# 4 Line ESD/EMI Protection for Color LCD Interfaces UM4401 DFN8 2.1×1.6

#### **General Description**

The UM4401 is a low pass filter array with integrated TVS diodes. It is designed to suppress unwanted EMI/RFI signals and provide electrostatic discharge (ESD) protection in portable electronic equipment. This state-of-the-art device utilizes silicon-avalanche technology for superior clamping performance and DC electrical characteristics. It has been optimized for protection of color LCD panels in cellular phones and other portable electronics.

The device consists of four identical circuits comprised of TVS diodes for ESD protection, and a RC network for EMI filtering. A series resistor value of  $100\Omega$  and a capacitance value of 10pF are used to achieve 25dB minimum attenuation from 800 MHz to 2.5GHz. The TVS diodes provide effective suppression of ESD voltages in excess of  $\pm 15kV$  (air discharge) and  $\pm 8kV$  (contact discharge) per IEC 61000-4-2, level 4.

The UM4401 is in a 8-pin, RoHS compliant DFN8 package. It measures 2.1mm×1.6mm. The leads are spaced at a pitch of 0.5mm and are finished with lead-free Ni Pd. The small package makes it ideal for use in portable electronics such as cell phones, digital still cameras, and PDAs.

#### **Applications**

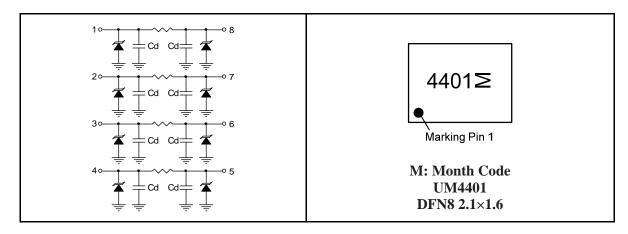
- EMI Filtering and ESD Protection for Data Lines
- Wireless Phones
- Handheld Products
- Notebook Computers
- LCD Displays

#### **Features**

- EMI/RFI Filter with Integrated TVS for ESD Protection
- ESD Protection to IEC 61000-4-2 (ESD) Level 4, ±15kV (Air), ±8kV (Contact)
- 25dB Minimum Attenuation: 800MHz to 2.5GHz
- Working Voltage: 5V
- Resistor:  $100\Omega \pm 15\%$
- Typical Capacitance:  $10pF (V_R=2.5V)$
- Solid-State Technology
- DFN8 Package: 2.1mm×1.6 mm
- Moisture Sensitivity Level 1

## **Pin Configurations**

## **Top View**





## **Ordering Information**

Part Number	Packaging Type	Marking Code	<b>Shipping Qty</b>	
UM4401	DFN8 2.1×1.6	4401	3000pcs/7Inch Tape & Reel	

## **Absolute Maximum Ratings (Note 1)**

Symbol	Parameter	Value	Unit
$T_{\mathrm{J}}$	Junction Temperature	125	°C
$P_R$	Steady State Power per Resistor @ 25°C	328	mW
$T_{OP}$	Operating Temperature Range	-40 to 85	°C
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_{\rm L}$	Γ <sub>L</sub> Maximum Lead Temperature for Soldering		°C

Note 1: Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

## **Electrical Characteristics** (T<sub>1</sub>=25°C unless otherwise noted)

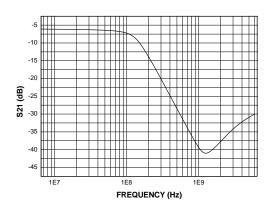
Symbol	Parameter	<b>Test Conditions</b>	Min	Тур	Max	Unit
$V_{RWM}$	Reverse Stand-Off Voltage				5.0	V
$V_{BR}$	Reverse Breakdown Voltage	I <sub>T</sub> =1.0mA	6 .0	7.0	8.0	V
$I_R$	Reverse Leakage Current	$V_{RWM}=3.3V$			100	nA
$R_{A}$	Total Series Resistance	I <sub>R</sub> =10mA Each Line	85	100	115	Ω
$C_d$	Total Capacitance	Input to GND, Each Line $V_R$ =0V, f=1MHz	16	20	24	pF
$C_d$	Total Capacitance	Input to GND, Each Line V <sub>R</sub> =2.5V, f=1MHz	9	10	12	pF
$f_{3dB}$	Cut-Off Frequency (Note 2)	Above this frequency, appreciable attenuation occurs		150		MHz

Note 2:  $50\Omega$  source and  $50\Omega$  load termination.

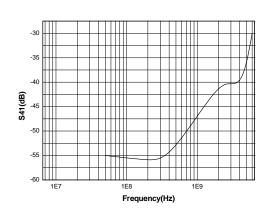


## **Typical Operating Characteristics**

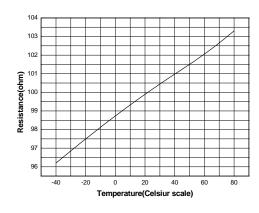
#### **Typical Insertion Loss S21**



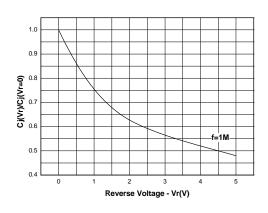
#### **Analog Crosstalk Curve (S41)**



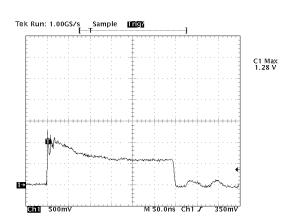
Typical Resistance vs. Temperature



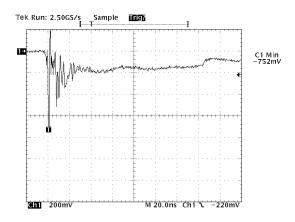
Capacitance vs. Reverse Voltage



ESD Clamping (+8kV Contact)



ESD Clamping (-8kV Contact)





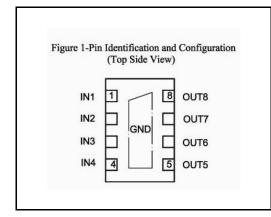
#### **Applications Information**

#### **Device Connection**

The UM4401 is comprised of four identical circuits each consisting of a low pass filter for EMI/RFI suppression and dual TVS diodes for ESD protection. The device is in a 8-pin DFN package. Electrical connection is made to the 8 pins located at the bottom of the device. A center tab serves as the ground connection. The device has a flow through design for easy layout. Pin connections are noted in Figure 1. All path lengths should be kept as short as possible to minimize the effects of parasitic inductance in the board traces. Recommendations for the ground connection are given below.

#### **Ground Connection Recommendation**

Parasitic inductance present in the board layout will affect the filtering performance of the device. As frequency increases, the effect of the inductance becomes more dominant. This effect is given by Equation 1.



Pin	Identification			
1 - 4	Input Lines			
5 - 8	Output Lines			
Center Tab	Ground			
Equation 1: The Impedance of an Inductor at Frequency XLF				

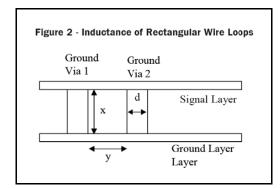
$$XLF(L,f) = 2 \times \pi \times f \times L$$

Where:

L= Inductance (H)

f = Frequency (Hz)

Via connections to the ground plane form rectangular wire loops or ground loop inductance as shown in Figure 2. Ground loop inductance can be reduced by using multiple vias to make the connection to the ground plane. Bringing the ground plane closer to the signal layer (preferably the next layer) also reduces ground loop inductance. Multiple vias in the device ground pad will result in a lower inductive ground loop over two exterior vias. Vias with a diameter d are separated by a distance y run between layers separated by a distance x. The inductance of the loop path is given by Equation 2. Thus, decreasing distance x and y will reduce the loop inductance and result in better high frequency filter characteristics.



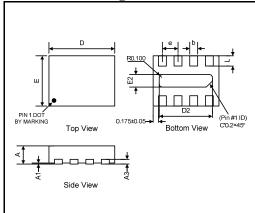
Equation 2: Inductance of Rectangular Wire Loop 
$$LRECT(d,x,y) = 10.16*10^{-9}*\left[x*ln\left[\frac{2*y}{d}\right] + y*ln\left[\frac{2*x}{d}\right]\right]$$
 Where: 
$$d = Diameter \ of \ the \ wire \ (in)$$
 
$$x = Length \ of \ wire \ loop \ (in)$$
 
$$y = Breath \ of \ wire \ loop \ (in)$$



# **Package Information**

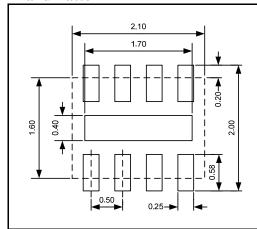
# **UM4401: DFN8 2.1×1.6**

**Outline Drawing** 



DIMENSIONS							
Cymbol	MILLIMETERS			INCHES			
Symbol	Min	Тур	Max	Min	Тур	Max	
A	0.50	0.575	0.605	0.020	0.023	0.024	
A1	0.00	-	0.05	0.000	-	0.002	
A3	0.15TYP		0.006TYP				
b	0.20	0.25	0.30	0.008	0.010	0.012	
D	2.05	2.10	2.175	0.081	0.083	0.086	
D2	1.60	1.70	1.80	0.063	0.067	0.071	
Е	1.55	1.60	1.675	0.061	0.063	0.066	
E2	0.30	0.40	0.50	0.012	0.016	0.020	
e	0.50TYP			0.020TYP			
L	0.275	-	0.38	0.011	-	0.015	

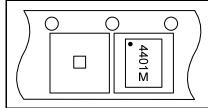
#### **Land Pattern**



#### NOTES:

- 1. Compound dimension: 2.10×1.60;
- 2. Unit: mm;
- 3.General tolerance  $\pm 0.05$ mm unless otherwise specified;
- 4. The layout is just for reference.

**Tape and Reel Orientation** 





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Union Semiconductor, Inc

Add: Unit 606, No.570 Shengxia Road, Shanghai 201210

Tel: 021-51093966 Fax: 021-51026018

Website: www.union-ic.com